

In the Claims:

Please amend the title on page 10 as follows:

What is claimed are:

Please cancel claim 6 without prejudice or disclaimer.

Please amend claims 1, 3 and 4 as follows:

Claim 1 (currently amended) A method of forming an oxynitride film, comprising the steps of:

loading a silicon substrate into an oxidization furnace;

~~implanting~~ injecting an oxygen based source gas into the oxidization furnace to grow a pure silicon oxide film on the silicon substrate;

~~blocking implantation of~~ stopping the injection of the oxygen based source gas and ~~implanting an~~ injecting inert gas into the furnace to ~~exhaust the~~ purge the oxygen based source gas remaining within the oxidization furnace;

raising a temperature within the oxidization furnace to a nitrification process temperature;

stabilizing the temperature within the oxidization furnace;

implementing a nitrification process for the pure silicon oxide film by ~~implanting~~ injecting a nitrogen based source gas; and

stopping ~~implantation~~ the injection of the nitrogen based source gas and ~~rapidly cooling the oxidization furnace while implanting the inert gas into the oxidization furnace~~ raising the temperature of the oxidization furnace to a temperature higher than the temperature at which the nitrification process is implemented before rapidly cooling the oxidization furnace while injecting inert gas into the oxidization furnace to thereby purge the nitrogen based source remaining in the furnace.

Claim 2 (original) The method as claimed in claim 1, wherein the nitrogen based source gas is a NH_3 , N_2O or NO gas.

Claim 3 (currently amended) The method as claimed in claim 2, wherein when the nitrification process is implemented, Ar or N_2 is ~~implanted~~ injected along with the nitrogen based source gas.

Claim 4 (currently amended) The method as claimed in claim 1, wherein the ~~nitrification process~~ temperature at which the nitrification process is implemented is higher than a temperature at which a viscous flow of a SiO₂ film ~~may happen~~ occurs ~~and the nitrification process is implemented at a temperature that is higher than the~~ ~~temperature at which the~~ to preclude viscous flow of the SiO₂ film ~~may happen in~~ ~~order and~~ to relax stress occurring that results when nitrogen is implanted into a Si-SiO₂ interface.

Claim 5 (original) The method as claimed in claim 1, wherein the nitrification process is implemented at a temperature higher than 800°C.

Claim 6 (canceled)